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	Code No: 132AA R16 R16	
	JAWAHARLAL NEHRU TECHNOLOGICAL UNIVERSITY HYDERABAD B.Tech I Year II Semester Examinations, August/September - 2017	
AG	ENGINEERING PHYSICS – II (Common/to EEE; ECE, CSE, EIE, IT) Max. Marks: 75	A
	Note: This question paper contains two parts A and B. Part A is compulsory which carries 25 marks. Answer all questions in Part A. Part B consists of 5 Units. Answer any one full question from each unit. Each question carries 10 marks and may have a, b, c as sub questions.	
AG	AG AG ART-AAG AG (25 Marks)	A
AG	1.a) Explain Heisenberg's uncertainty principle. b) Give significance of wave function. c) What is direct and indirect band gap semiconductors. Explain the I-V characteristics of PN junction diode. Define Electric susceptibility and polarizability. (2] (3) (4) Explain the I-V characteristics of PN junction diode. (5) (6) Define Electric susceptibility and polarizability. (7) (8) (9) Define Magnetic field induction and Magnetic susceptibility. (9) (1) (1) (2) (3) (4) (5) (6) (7) (7) (7) (8) (9) (9) (1) (1) (1) (1) (2) (3) (4) (4) (5) (6) (7) (7) (8) (9) (9) (1) (1) (1) (1) (2) (3) (4) (4) (5) (6) (7) (7) (7) (8) (9) (9) (1) (1) (1) (1) (2) (3) (4) (4) (5) (6) (7) (7) (7) (8) (9) (9) (9) (1) (1) (1) (1) (2) (2) (3) (4) (4) (5) (6) (7) (7) (7) (8) (9) (9) (9) (1) (1) (1) (1) (2) (2) (3) (4) (4) (5) (6) (7) (7) (7) (8) (9) (9) (9) (1) (1) (1) (1) (1	<u> </u>
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	2.a) Explain de-Broglie hypothesis. Explain G.P. Thompson's experiment in support of this	
AG	hypothesis. b) Write the conclusion of Kronig-Penny model. Using this model show that the energy spectrum of an electron contains number of allowed states separated by forbidden bands. OR	Д
	3.a) Describe the Davisson and Germer's experiment and explain how it enabled the verification of wave nature of matter.	
	b) Derive time independent schrodinger's wave equation for a free particle. [5+5]	
AG	4.a) Calculate the carrier concentration in n-type semiconductor. b) Explain the energy level diagram of a PN junction diode and the energy level diagram of biased PN junction. OR	A
	5.a) Calculate the carrier concentration in intrinsic semiconductor.b) Explain the diode equation. [5+5]	
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	medium			ization and electr	ric sucectibity of	the dielectric	
AG		internal field? Do	OR	nethod to calcula	te the internal fi	[5+5]	<u></u>
		the origin of M					
AG	b) Explain flux qua 9.a) Explain	superconductivity ntization and coo Hysteresis curve Meissner Effect?	per pairs? OR based on domain	theory.	AĞ		<u> </u>
	h) Damlain	e nanomaterials. I construction and	working of CEM			[5+5]	
AG	11.a) Explain b) Explain	CVD and Ball mi construction and	OR lling method for working of TEM	synthesis of nanc	omaterials.	<u></u>	A
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